Study of the Single-Event Effect on the SALT Chip

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Test Beam Setup (1) Main equipment 1 SALT board + 1 VLDB 0 ard 0 1 SALT board + 1 VLDB 0 ard 0 1 InuxPC 1 1 SALT board + 1 VLDB 0 1 Rasperry Pi3 compute 0 1 Rasperry Pi3 compute 1 1 Salt board + 1 VLDB 0 1 Rasperry Pi3 compute 1 1 Salt board + 1 VLDB 0 1 Rasperry Pi3 compute 1 1 Salt board 1 1 Salt 1 board 1 1 3 3 2 0 1 3 1 2 E 7 0 0 0 3 3 6 3 0 4 0 2 8 3 0 4 0 2 8 3 0 1 1 0 0 5 7 1 8 1 1 7 2 5 7 - 1 4 1 1 3 2 0 1 3 1 2 E 7 0 0 0 3 3 6 3 0 4 4 0 2 8 3 1 4 3 4 3 6 1 0 3 E 9 1 0 0 7 5 9 6 6 1 7 3 8 2 - 1 1 1 5 5 5 3 1 1 0 3 E 9 1 0 0 7 5 9 6 6 1 7 3 8 2 - 1 1 1 5 5 5 3 1 1 0 3 E 9 1 0 0 7 5 9 6 6 1 7 3 8 2 - 1 1 1 5 5 5 3 1 1 0 3 E 9 1 0 0 7 5 9 8 6 6 1 7 3 8 2 - 1 1 1 5 5 5 3 1 1 0 3 E 9 1 0 0 7 5 9 8 6 6 1 7 3 8 2 - 1 1 1 5 5 5 3 1 1 0 3 E 9 1 0 0 7 5 9 8 6 6 1 7 3 8 2 - 1 1 1 5 5 5 3 1 1 0 3 E 9 1 0 0 7 5 9 8 6 6 1 7 3 8 2 - 1 1 1 5 5 5 3 1 1 0 3 E 9 1 0 0 7 5 9 8 6 6 1 7 3 8 2 - 1 1 1 5 5 5 5 1 1 0 3 E 1 0 0 0 7 5 5 9 8 6 6 1 7 3 8 2 - 1 1 1 5 5 5 5 5 5 1 1 0 3 E 1 0 0 0 7 5 5 9 6 6 1 7 3 8 2 - 1 1 1 5 5 5 5 5 5 5 1 1 0 3 E 1 0 0 0 7 5 5 9 6 6 1 7 3 8 2 - 1 1 1 5 5 5 5 5 5 5 1 1 0 3 E 1 0 0 0 7 5 5 9 8 6 6 1 7 3 8 2 - 1 1 1 5 5 5 5 5 5 5 1 0 3 2 - 1 1 5 5 5 5 5 5	Register cor • SALT V3.9 wa • All TrimDAC, 0×AA. In the I ADC value fro Addre 206-28 115-19 105-17 307-37 205 286-28 • Here are all S Run Regi 3 154 5 190 AA 14F 5 190 4 14F 6 26F 144 AA 144 AA 140 AA 141 AA 142 AA 144 AA 140 AA 141 AA 142 AA 144 AA 140 AA 141 AA 142 AA 143 AA 144 AA 140 AA 141 AA 142 AA 130 AA <	Ifiguration & Rate of SEUsis configured to a normal running conditionPedestal, KillMask & InjectMask were setast run KillMask = 0×00 , so as to read outmail channels.Setus in the Configuration Registers.Vnew Nbit Ch004004004012023033041000400401402303304110040040140230330411054063074083094004004014023030E0411054051061074083094004014023030E0415051610516106161071610811091109110911001100110011001 </th <th>to to to to to to to to to to to to to t</th> <th>ADC SEUS $\int_{0}^{0} \int_{0}^{0} \int_{0$</th>	to to to to to to to to to to to to to t	ADC SEUS $\int_{0}^{0} \int_{0}^{0} \int_{0$
 for each intensity value. A run lasts 600s. Total 7 runs were taken. In the 	D	4 changes.		• 2 memory SEUs are observed. One has a bit change of " $1 \rightarrow 0$ ". The other has a " $0 \rightarrow 1$ ".
last run the Kill Mask was disabled, to test ADC	Reg	gister SEU Test (a)CIAE		• We are curious about the result of memory SEU, so
 readout. The total fluence for SEU test is 1.48×10¹³ cm⁻², 45.5% with KillMask disabled. 		Register		more about memory SEU. This will be covered in the following section. 5
5		and Rate of		Motivation of radiation test
Introduction		SFLIS		• SALT V3.5 is vulnerable to radiation in
• UT(Upstream Tracker) is a new silicon		ADC at	nd	its TrimDAC and Pedestal registers.
tracker TT.	Test Beam	Memo	ry	This was first observed at the MGH
• It has 4 layers, each layer consists of 16/18	Setup (1)	SEUs	5	further confirmed at the PSI radiation test
staves, and each stave consists of 14/16		Study of		on Nov 3rd, 2019.
hybrids.				• After careful studies, a possible solution

- was found and implemented in a new



the Single-Event Effect Rate of on the SALT Chip Memory Test Beam SEUs, TID Setup (2) and Special Two Events Configuration Modes and Calculation Model Memory SEU Test @CSNS Two Configuration Modes & Calculation Model • SALT V3.9 was set to a special mode that the ADC value is constant 0x15. Number Value ADC use constant value 0x15 0x55 100 Output NZS after pedestal subtraction 103 0x40 206-285 128 0x80 TrimDac 115-194 0x00 Pedestal

307-316 0x00 Inject Mask In order to calculate the rate of SEUs occurring during memory or data transfer, we planned two different configurations, difference between which is the time of data in the memory~6 times. DAQ Configuration: \Box MEP size of N × 480 BXs. \Box TFC sequence= 6*(1 NZS + 79 HeaderOnly). Average time in memory: 81.4*25ns TFC sequence= (1 NZS + 79 HeaderOnly). Average time in memory: 14.4*25ns

Kill Mask

0x00

105-114

16

design release, SALT V3.9. It needs to be validated in the test. • SALT V3.9 was also tested twice.

The first was at the **CIAE**(China Institute of Atomic Energy) on Dec 31, 2020. The second was at the **CSNS**(China Spallation Neutron Source) from Oct 18 to 25, 2021.

Rate of Memory SEUs

The cross section of data during transfer is much larger(~100 times) than that in memory. Take the cross section of **data transfer as the** total cross section.

• The SEU rate of the per channel in data transfer: a) cross section $\sigma_{total} = 5.9 \times 10^{-14} cm^2$.

b) SEU rate in the UT innermost region = 3.5×10^{-7} Hz

c) SEU rate if the whole UT uses SALT V3.9

= **3.7 / Day** Data transfer SEUs.





Memory-dominated Mode Transfer-dominated Mode During the process of fetching data, the beam flux was maintained at $3.4 \times 10^9 p/cm^2/s$. There are 10 and 7 SEUs observed in the two modes respectively.

• Model $\begin{array}{ll} N^{RAM} \propto T \times \sigma_{RAM} \times fluence & N_1 = N_1^{RAM} + N_1^{Trans} \\ N^{Trans} \propto \sigma_{Trans} \times fluence & N_2 = N_2^{RAM} + N_2^{Trans} \end{array}$ N^{RAM}



- The 1st event was that 000000 were inserted in the middle of the data.
- The 2nd event was that BXID was one less count. Until the next BxReset, the data get right. Acknowledgements
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